FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))	Attorney Docket No.: MUH-12837 Appl. No.: Applicant: DIETMAR GOGL ET AL. Filing Date: October 14, 2003 Group Art Unit:

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
LP	A	5,703,805	12/30/97	Tehrani et al.			
LP	B	6,359,829 B1	3/19/02	Van Den Berg			
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES	TRANSL. NO
LP	J	1 003 176 A2	5/24/00	Europe				
LP	K	2000187976	7/4/00	Japan				
	L							
	M							
	N							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

LP		Wang, Z. G. et al.: "Design, Simulation, and Realization of Solid State Memory Element Using the Weakly Coupled GMR Effect", IEEE Transactions on Magnetics, Vol. 32, No. 2, March 1996, pp. 520-526
LP		Zheng, Y. et al.: "Micromagnetic Principles in Pseudo Spin Valve Memory Element Design", IEEE Transactions on Magnetics, Vol. 33, No. 5, September 1997, pp. 3286-3288

EXAMINER	DATE CONSIDERED
	06/03/04

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

LP		Wang, Z. et al.: "Quarternary Giant Magnetoresistance Random Access Memory", American Institute of Physics, J. Appl. Phys., Vol. 79, No. 8, April 15, 1996, pp. 6639-6641
LP		Wang, Z. G. et al.: "Feasibility of Ultra-Dense Spin-Tunneling Random Access Memory", IEEE Transactions on Magnetics, Vol. 33, No. 6, November 1997, pp. 4498-4512

EXAMINER	DATE CONSIDERED
[signature]	05/01/04